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Author Correction: High-temperature-resistant silicon-polymer hybrid modulator operating at up to 200 Gbit s⁻¹ for energy-efficient datacentres and harsh-environment applications

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Correction to: *Nature Communications* <https://doi.org/10.1038/s41467-020-18005-7>, published online 24 August 2020.

The original version of this Article contained an error in Fig. 1c. The length of the silicon core at the center of the panel was incorrectly labelled as '4 mm', rather than the correct '4 μm'. This has been corrected in both the PDF and HTML versions of the Article.

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